



安徽富信半导体科技有限公司

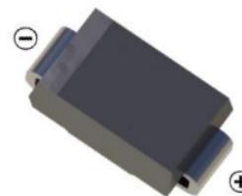
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

S2A-S2M

SMB General Purpose Rectifier Diode 通用整流二极管

■Features 特点

Low forward voltage drop 低正向压降
 Low reverse leakage current 低反向漏电流
 High surge current capability 高浪涌电流能力
 Surface mount device 表面贴装器件
 Case 封装:SMB



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	S2A	S2B	S2D	S2G	S2J	S2K	S2M	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	2							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	60							A
Thermal Resistance Junction-Lead 结到管脚热阻	$R_{\theta JL}$	16							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$							

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	V_F			1.1	V	$I_F=2\text{A}$
Reverse Current($T_A=25^{\circ}\text{C}/$) 反向电流($T_A=125^{\circ}\text{C}/$)	I_R			5 200	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		30		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

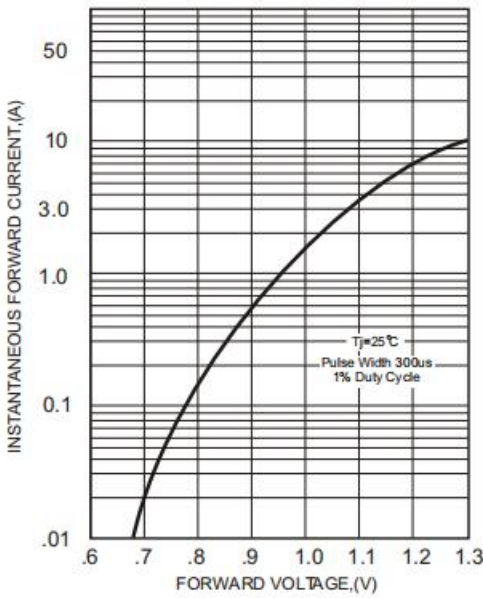


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

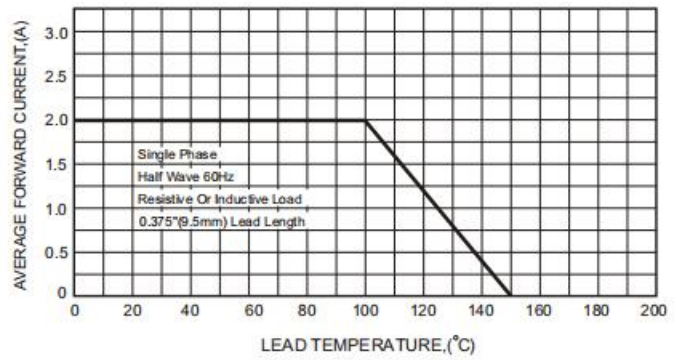


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

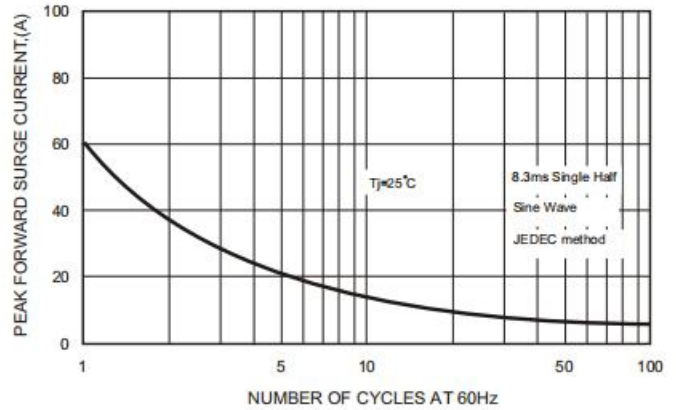


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

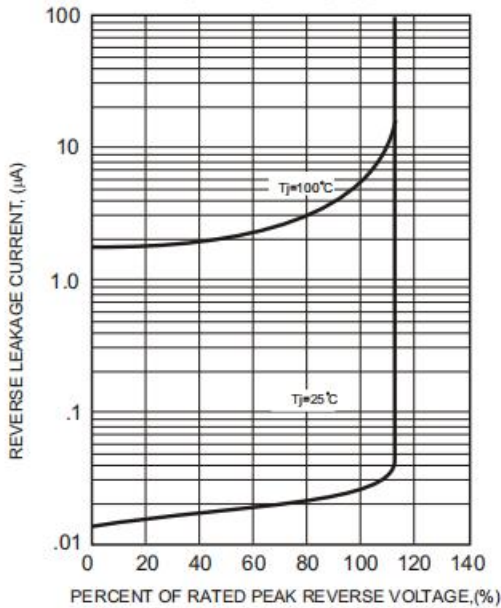
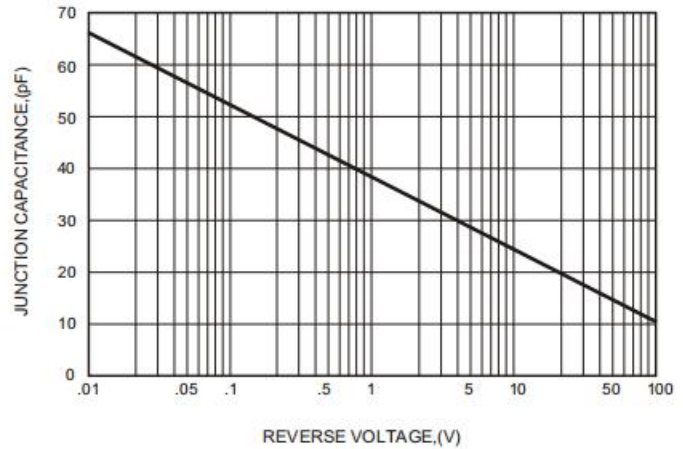
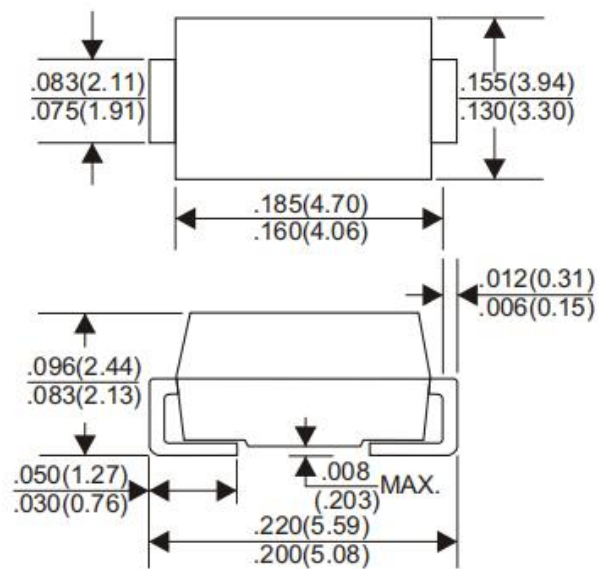


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in inches and (millimeters)